TIL156, TIL157A OPTOCOUPLERS

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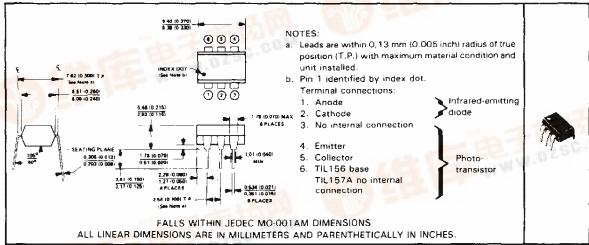
SOOS047A D2492, SEPTEMBER 1978-REVISED JUNE 1989

UL LISTED - FILE #E65085

- GaAs-Diode Light Source Optically Coupled to a Silicon N-P-N
 Darlington-Connected Phototransistor
- High Direct-Current Transfer Ratio . . . 300% Minimum at 10 mA
- Plug-in Replacement for TIL113 and TIL119A
- High-Voltage Electrical Isolation . . . 2500 V RMS (3535 V Peak)
- No Base Connection on TIL157A for Environments with High Electromagnetic Interference

mechanical data

The package consists of a gallium arsenide infrared-emitting diode and an n-p-n silicon darlington-connected phototransistor mounted on a 6-lead frame encapsulated within an electrically nonconductive plastic compound. The case will withstand soldering temperature with no deformation and device performance characteristics remain stable when operated in high humidity conditions, Unit weight is approximately 0.52 grams.



absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-Output RMS Voltage (See Note 1)		2500 V
Collector-Base Voltage (TIL156)		30 V
Collector-Emitter Voltage (See Note 2)		30 V
Emitter-Collector Voltage		7 V
Emitter-Base Voltage (TIL156)		7 V
Input-Diode Reverse Voltage		
Input-Diode Continuous Forward Current at (or below) 25°C Free-Air Temperature (See Note 3)		
Continuous Phototransistor Power Dissipation at (or below) 25°C Free-Air Temperature (See Note 4)		150 mW
Storage Temperature Range	– 55°C	to 150°C
Lead Temperature 1,6 mm (1/16 inch) from Case for 10 Seconds		

- NOTES 1 This rating applies for sine-wave operation at 50 or 60 Hz. Service capability is verified by testing in accordance with UL requirements
 - 2. This value applies when the base emitter diode is open-circuited.
 - 3. Denate linearly to 100° C free-air temperature at the rate of 1.33 mA/ $^{\circ}$ C.
 - 4. Denate linearly to 100°C free-air temperature at the rate of 2 mW/°C.



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electrical characteristics at 25°C free-air temperature

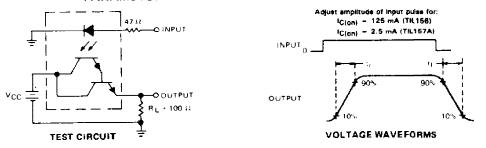
PARAMETER		TEST CONDITIONS			TIL156			TIL157A			UNIT	
					MIN	TYP	MAX	MIN	TYP	MAX	UNII	
V(BR)CBO	Collector-Base Breakdown Voltage	I _C = 10 μA,	I _E - 0,	IF = 0	30						٧	
V(BR)CEO	Collector-Emitter Breakdown Voltage	IC = 1 mA,	ig = 0,	IF = 0	30			30			٧	
V(BR)EBO	Emitter-Base Breakdown Voltage	ig = 10 μA,	IC = 0.	1F = 0	7						٧	
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	IE = 10 μA,	le * 0					7			٧	
I _R	Input Diode Static Reverse Current	V _R = 3 V					10			10	μΑ	
[‡] C(on)	On-State Collector Current	V _{CE} = 1 V, V _{CE} = 1 V,	ig = 0, ig = 10 mA	lp = 10 mA	30	100		30	160		mA	
[[] C(off)	Off-State Collector Current	V _{CE} = 10 V,	1 _B = 0,	i _F = 0			100			100	nA	
hFE	Transistor Static Forward Current Transfer Ratio	V _{CE} = 1 V,	IC = 10 mA,	IF = 0		15 000						
٧F	Input Diode Static Forward Voltage	I _F = 10 mA					1.5			1.5	V	
VCE(sat)	Collector-Emitter Saturation Voltage	I _C = 125 mA, I _C = 30 mA,	I _B = 0, I _F = 10 mA	1 _F = 50 mA			1.2			1	٧	
10	Input-to-Output Internal Resistance	V _{in-out} = 500 V,	See Note 5		1011	_		1011			Ω	
Cio	Input-to-Output Capacitance	V _{in-out} ≠ 0,	f = 1 MHz,	See Note 5		1	1.3		1	1.3	pF	

Note 5: These parameters are measured between both input diode leads shorted together and all the phototransistor leads shorted together. †References to the base are not applicable to the TIL157A.

switching characteristics at 25°C free-air temperature

PARAMETER		TEST CONDITIONS†		TIL156			TIL157A			UNIT
		168	MIN	TYP	MAX	MIN	TYP	MAX	Citi	
tr	Rise Time	V _{CC} = 15 V,	IC(on) = 125 mA,		300]
tş	Fall Time	R _L = 100 Ω.	See Figure 1		300				-	μs
tr	Rise Time	V _{CC} = 10 V,	I _{Clon)} = 2.5 mA,					300		
tį	Fall Time	R _L = 100 Ω,	See Figure 1					300		گلاز

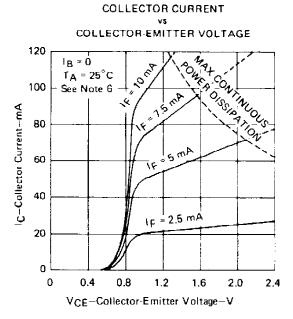
PARAMETER MEASUREMENT INFORMATION



- NOTES: a. The input waveform is supplied by a generator with the following characteristics: Z_{out} < 50 Ω, τ_r ≤ 15 ns, duty cycle ≈ 1%, t_W = 500 μs.
 b. The output waveform is monitored on an oscilloscope with the following characteristics: τ_r ≤ 12 ns, A_{in} ≥ 1 MSS, C_{in} ≤ 20 pF.

FIGURE 1-SWITCHING TIMES

TYPICAL CHARACTERISTICS



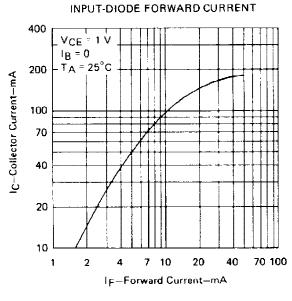
COLLECTOR CURRENT COLLECTOR-EMITTER VOLTAGE 200 180 160 C-Collector Current-mA = 30 mA 140 = 40 mÅ 120 ||F = 50 mA 100 80 60 40 1_B = 0 $T_A = 25^{\circ}C$ 20 See Note 6 0 0.2 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 2 VCE-Collector-Emitter Voltage-V

FIGURE 2

COLLECTOR CURRENT



FIGURE 3



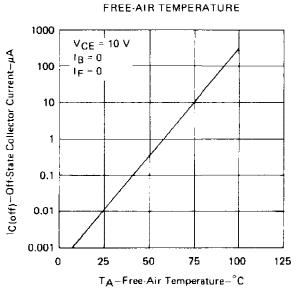


FIGURE 4

FIGURE 5

NOTE 6. Pulse operation of input diode is required for operation beyond limits shown by dotted line.



TYPICAL CHARACTERISTICS

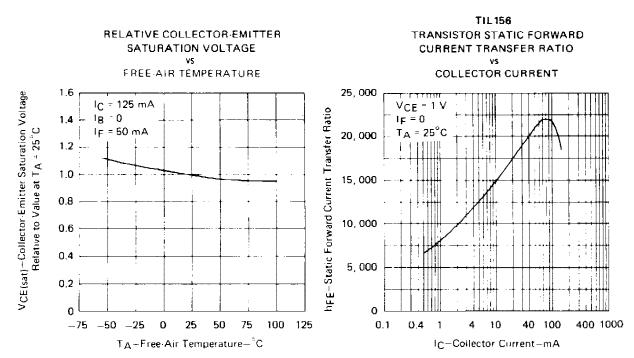
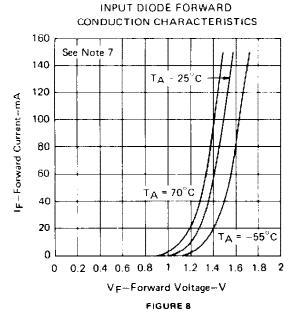


FIGURE 6



NOTE 7: This parameter was measured using pulse techniques, $t_{\rm W} \sim 1$ ms, duty cycle $\leq 2\%$.

FIGURE 7

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